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Spin-Dependent Electronic States of the Ferromagnetic Semimetal EuB$_6$

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The spin polarization of EuB$_6$ has been measured by using Andreev reflection spectroscopy. Analyses of the conductance spectra of the EuB$_6$/$Pb$ junctions yield a spin polarization of about 56%. The results demonstrate that the ferromagnetic EuB$_6$ is not half-metallic. Combined with the Hall effect and magnetoresistivity data, the results indicate a semimetallic band structure with a fully spin-polarized hole band and an unpolarized electron band. The values and the spread of the measured spin polarization are quantitatively consistent with the experimentally determined Fermi surface and carrier densities.

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To define the contact region between EuB₆ and Pb, a 50 nm-thick layer of SiO₂ was sputter-deposited on the top surface of the single crystal through a shadow mask, leaving a gap of 0.1 mm. A 0.1 mm-wide Pb stripe with a thickness of about 500 nm was then thermally evaporated across the gap. For some small crystals, we used Stycast 1266 epoxy to extend beyond the size of the crystal as shown in Fig. 1(b).

The zero-bias junction resistance versus temperature (R_j versus T) and the conductance spectra (dI/dV versus V) were measured in a ³He cryostat by using phase-sensitive lock-in detection. The normal state junction resistances of our samples varied from several Ohms to about 1000Ω. The residual resistivity of EuB₆ is very small, as shown in the left inset in Fig. 2. Specifically, for the EuB₆ specimens used, the contribution from the crystal is calculated to be less than 0.2 Ω. The EuB₆/In contact is at least 100 times larger than the EuB₆/Pb junction. More importantly, the R_j versus T curves (one is shown in Fig. 2) always clearly reflected the superconducting transition of Pb at ~7 K but did not exhibit any features at the In transition (3.4 K). Therefore, the measured R_j is dominated by the EuB₆/Pb junction. The conductance spectrum of a normal-metal/superconductor (N/S) junction is well described by the theory of Blonder, Tinkham, and Klapwijk (BTK) [18], in which the spectrum is determined by the barrier strength, described by a dimensionless parameter Z. For ferromagnet/superconductor (FM/S) junctions, the conductance spectrum is modified by the suppression of AR due to the spin imbalance in the FM [19]. The fitting of the modified spectrum, with Z and P as the fitting parameters, thus gives reliable determination of P for the FM [20].

Figures 3(a) and 3(b) show the normalized conductance spectra of an EuB₆/Pb junction at two different temperatures. The normalization of each curve was based on a corresponding sweep at a magnetic field slightly higher than the critical field of the Pb film. Figure 3(a) shows the spectrum measured at 1.4 K and the best fit to the spin-polarized BTK model. The actual measurement temperature (1.4 K) and an expected energy gap (Δ) value of 1.32 meV were used in the fitting. The best fit yields Z = 0.52 and P = 47% with a certainty better than 2%. Figure 3(b) shows the spectrum of the same sample at 0.35 K. Without changing any parameters used in fitting the spectrum at 1.4 K, a spin-polarized BTK conductance curve was generated with T = 0.35 K. The theoretical curve matches the experimental data very well [Fig. 3(b)]. The consistency in the obtained P and Z values is expected because both parameters should be temperature-independent in this range. Finally, theoretical values of the normalized zero-bias conductance at different temperatures were calculated from the spin-polarized BTK model with Z = 0.52 and P = 47% (right inset in Fig. 2): There is good agreement between the calculated values and the experimental data over the entire temperature range.

Similar measurements and analyses were performed on seven different EuB₆/Pb junctions, and the P values obtained are 47%, 64%, 57%, 56%, 58%, 54%, and 65%, which cluster around 56% with a spread of approximately ±9%. The Z values of the junctions cover a relatively broad range from 0.29 to 1.0. There is no apparent correlation between P and Z, and we did not observe any
indication of the decline of $P$ with increasing $Z$, consistent with our previous observations in other planar junctions [21] and in contrast to the effect often seen in point contact experiments [22]. The results are in clear contradiction with the half-metallic picture as a possible outcome of the LDA + $U$ calculations [13,14]. With a two-pocket Fermi surface [7,8], $P$ near 50% is consistent with the picture of one band being fully spin-polarized while the other is unpolarized. A fully polarized CB is the scenario predicted by earlier LDA calculations [3]. However, the opposite situation with a fully polarized VB is also possible.

In order to further clarify the spin-dependent band structure of EuB$_6$, we carried out MR and HE measurements on a 4.0 × 2.2 × 0.1 mm$^3$ platelet from the same batch. The data are shown in Figs. 4(a) and 4(b). The MR, which peaks around $T_c$, becomes positive below $T_c$. In Fig. 4(b), there appear to be two temperature regimes where the Hall slope takes on two distinct values, with a large (small) Hall slope for high (low) temperatures. At intermediate temperatures, there is a transition from the large slope to the small slope with increasing applied field, and the switching field decreases with decreasing temperature. Qualitatively similar features in the MR and HE were observed by Wigger et al. [11]. The switch in the Hall slope with decreasing temperature across $T_c$ and with increasing field, and the switching field decreases with decreasing temperature. With the stability at low temperatures, we use the standard two-band model to simultaneously describe the MR and the Hall coefficient [23]:

$$\rho = \frac{\sigma_e + \sigma_p + \sigma_e \sigma_p (\sigma_e R_e^2 + \sigma_p R_p^2) B^2}{(\sigma_e + \sigma_p)^2 + \sigma_e^2 \sigma_p^2 (R_e + R_p)^2 B^2},$$

(1)

$$R_H = \frac{\rho_H}{B} = \frac{R_e \sigma_e^2 + R_p \sigma_p^2 + \sigma_e^2 \sigma_p^2 R_e R_p (R_e + R_p) B^2}{(\sigma_e + \sigma_p)^2 + \sigma_e^2 \sigma_p^2 (R_e + R_p)^2 B^2},$$

(2)

where $R_e$, $R_p$, $\sigma_e$, and $\sigma_p$ are the Hall coefficients and conductivity for the electrons and holes, respectively. To eliminate the influence of the small kink of MR at low fields and the oscillations at high fields, we fit the curves for 5.6 K in a magnetic field range from 2.0 to 6.0 T and then plotted the fits in the entire field range, as shown in Figs. 4(c) and 4(d). Obviously, there is excellent agreement for both curves. The fitting parameters are listed in Fig. 4(c). From the resulting Hall coefficients for electrons and holes, we obtain the carrier density for each band: $n_e = 3.23 \times 10^{19}$ cm$^{-3}$ and $n_p = 3.05 \times 10^{19}$ cm$^{-3}$, respectively. These values are close to the carrier densities obtained through two-band analysis by Wigger et al. [11]; especially, the $n_e/n_p$ ratio is almost the same.

In the paramagnetic phase, the low field Hall coefficients $R_H|_{B=0}$ indicate an electronlike effective carrier density of $n_{eff} = 2.70 \times 10^{19}$ cm$^{-3}$ in zero field. With a semiconducting band structure, these carriers would all be electrons; the holes in the ferromagnetic phase at low temperatures would have to come from a spin splitting of the VB with the spin-up branch crossing the chemical potential. In this scenario, however, all missing electrons in the VB would end up in the CB; hence, the electron-hole imbalance would be the same in both phases. This is clearly contradicted by the $n_e$ and $n_p$ at low temperatures determined above. We therefore conclude that EuB$_6$ has a semimetallic band structure even in the paramagnetic phase. In this picture, with comparable $R_e$ and $R_p$, the dominance of electrons in the HE implies that $\sigma_p/\sigma_e \ll 1$, which suggests localization of the holes in the paramagnetic phase. A natural conclusion from this observation is that it is the localized holes that form the bound magnetic polarons via exchange interaction with the Eu$^{2+}$. At low temperatures and/or high fields, the alignment of the Eu$^{2+}$ moments leads to overlap of the magnetic polarons and delocalization of the holes and, consequently, a large spin splitting of the VB. This conclusion is corroborated by the results of Goodrich et al. [7], who identified the holes in the VB as spin-polarized based on their analysis of the amplitude of the quantum oscillations. Further, a substantial splitting of the VB was recently observed directly.
through ARPES [24]. Taken together, the measured spin polarization and the analyses of HE and MR strongly suggest semimetallic band structures for EuB$_6$ in both paramagnetic and ferromagnetic phases; in the ferromagnetic state, a large spontaneous Zeeman splitting of the valence band leads to fully spin-polarized holes and unpolarized electrons.

This picture provides a physical model from which quantitative calculation of $P$ is possible based on the experimentally determined ellipsoidal pockets of electrons and holes. As pointed out by Mazin [16], $P$ measured by AR spectroscopy not only has to do with the density of states (DOS) at the Fermi level but also depends on the size and shape of the Fermi surface. In particular, for an Andreev junction in the diffusive limit (as in our case), the measured $P$ corresponds to a value with spin densities weighted by $v_{F\parallel}^2$:

$$P_{Nv^\parallel} = \frac{\langle Nv^2 \rangle - \langle Nv^2 \rangle}{\langle Nv^2 \rangle} + \langle Nv^2 \rangle, \quad (3)$$

where $N$ is the DOS at the Fermi surface and $v$ the Fermi velocity. Starting from the Fermi surface of EuB$_6$ mapped out by quantum oscillation measurements [7,8], we calculate $P_{Nv^\parallel}$ and compare with the measured values here.

Although there were slight inconsistencies between different experiments, various dHvA [7,8] and SdH [8] measurements have identified an electron and a hole ellipsoid pocket centered at the X point, each with a pair of frequencies corresponding to the minimum and maximum extremal areas of the ellipsoids. From the angular dependence of the frequencies, Aronson et al. [8] were able to determine the volumes of the electron and hole pockets and, consequently, electron and hole densities of 1.20 $\times$ 10$^{20}$ and 2.03 $\times$ 10$^{20}$ cm$^{-3}$, respectively. The densities were calculated without considering any spin polarization. If the larger pocket is populated by spin-up holes and the smaller pocket is equally occupied by spin-up and spin-down electrons, the results of Ref. [8] then yield hole and electron densities of 1.01 $\times$ 10$^{20}$ and 1.20 $\times$ 10$^{20}$ cm$^{-3}$, respectively, much closer to full compensation. With this quantitative picture, we calculate $P_{Nv^\parallel}$ by integrating over the entire Fermi surface and obtain $P_{Nv^\parallel} = 49.8$. On the other hand, the two-band model fits to our low temperature HE and MR data yielded carrier densities of 3.23 $\times$ 10$^{19}$ and 3.05 $\times$ 10$^{19}$ cm$^{-3}$ for electrons and holes, respectively. With a fully polarized VB and an unpolarized CB, and by maintaining the shapes of the two ellipsoidal pockets of Aronson et al. [8], these densities result in $P = 53\%$.

Because the small Fermi surface and intrinsic carrier densities ($\sim$ 10$^{-3}$ per unit cell) in EuB$_6$, small fluctuations in sample stoichiometry can lead to sizable changes in electron and hole densities as well as the extent of the inequalities between them. Previous quantum oscillation [7,8] and HE [11] measurements have revealed such variations. Variations in the degree of compensation change the relative sizes of the electron and hole pockets and, consequently, the overall $P$. In fact, a small variation of the degree of compensation can account for the spread in the $P$ values we observed: Based on the band structure we have deduced and the shapes of the measured ellipsoidal electron and hole pockets by Aronson et al. [8], the range of $P$ values corresponds to $n_e/n_c$ from 0.75 ($P = 47\%$) to 1.28 ($P = 65\%$).

In summary, the spin polarization of EuB$_6$ crystals has been determined by AR spectroscopy, and the obtained values are in the range of 56% ± 9%, which directly contradicts the half-metallic band structure. The results of spin polarization, transport, and Fermi surface measurements provide a quantitatively consistent picture in agreement with a semimetallic band structure with a substantial band splitting for the valence band only in the ferromagnetic state.

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